

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

SFT1345 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1=210m Ω (typ.)
- · 4V drive

- Input Capacitance Ciss=1020pF(typ.)
- · Halogen free compliance

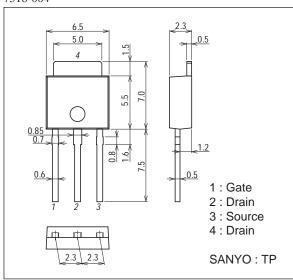
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-100	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		-11	А
Drain Current (PW≤10μs)	IDP	PW≤10μs, duty cycle≤1%	-44	А
Allowable Power Dissipation	D-		1.0	W
	PD	Tc=25°C	35	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

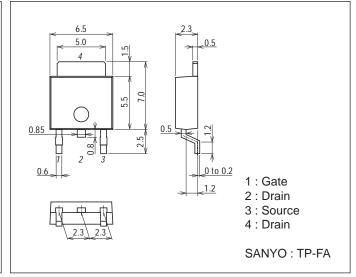
Package Dimensions

unit : mm (typ) 7518-004



Package Dimensions

unit : mm (typ) 7003-004



Product & Package Information

• Package : TP

• JEITA, JEDEC: SC-64, TO-251, SOT-553

• Minimum Packing Quantity: 500 pcs./bag

Marking(TP, TP-FA)



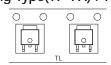
Product & Package Information Electrical Connection

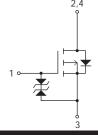
• Package : TP-FA

• JEITA, JEDEC: SC-63, TO-252, SOT-428

• Minimum Packing Quantity: 700 pcs./reel

Packing Type(TP-FA): TL





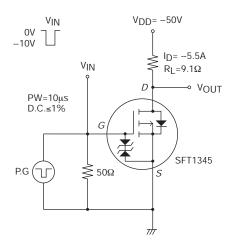
SANYO Semiconductor Co., Ltd.

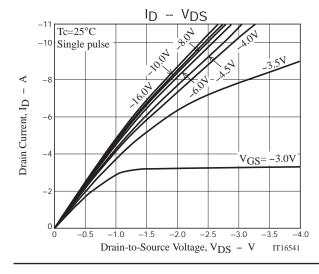
http://semicon.sanyo.com/en/network

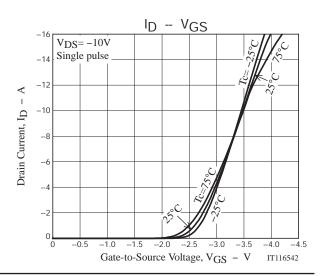
Electrical Characteristics at Ta=25°C

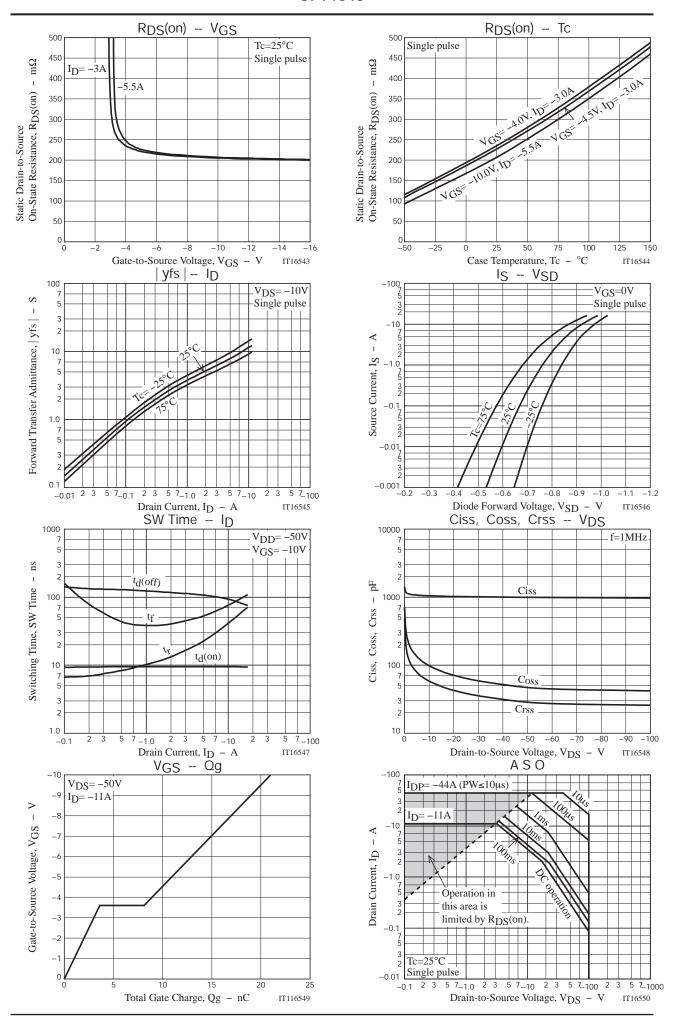
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-100V, V _{GS} =0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	٧
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-5.5A		8.5		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-5.5A, V _G S=-10V		210	275	mΩ
	R _{DS} (on)2	I _D =-3A, V _G S=-4.5V		225	315	mΩ
	R _{DS} (on)3	I _D =-3A, V _G S=-4V		235	330	mΩ
Input Capacitance	Ciss	V _{DS} =-20V, f=1MHz		1020		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		72		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-20V, f=1MHz		43		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		9.5		ns
Rise Time	tr	See specified Test Circuit.		25		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		105		ns
Fall Time	tf	See specified Test Circuit.		55		ns
Total Gate Charge	Qg	V _{DS} =-50V, V _{GS} =-10V, I _D =-11A		21		nC
Gate-to-Source Charge	Qgs	V _{DS} =-50V, V _{GS} =-10V, I _D =-11A		3.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V _D S=-50V, V _G S=-10V, I _D =-11A		4.5		nC
Diode Forward Voltage	V _{SD}	I _S =-11A, V _G S=0V		-0.93	-1.5	V

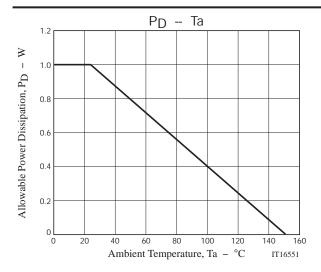
Switching Time Test Circuit

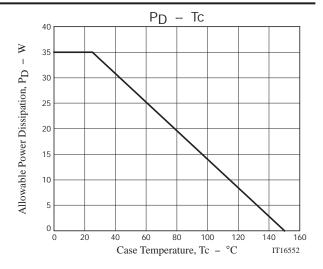












Note on usage: Since the SFT1345 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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